

## General Description

The WSP16N10 is the highest performance trench N-Ch MOSFET with extreme high cell density, which provide excellent  $R_{DS(on)}$  and gate charge for most of the synchronous buck converter applications.

The WSP16N10 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

## Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent  $C_{dv}/dt$  effect decline
- Green Device Available

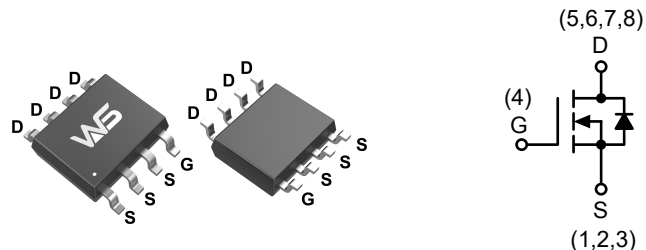
## Product Summary

$BV_{DSS}$	$R_{DS(on)}$	$I_D$
100V	8.9mΩ	16A

## Applications

- DC/DC Converter

## SOP-8L Pin Configuration



## Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	100	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	16	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	10	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	56	A
EAS	Single Pulse Avalanche Energy <sup>3</sup> L=0.1mH	30	mJ
$I_{AS}$	Avalanche Current	28	A
$P_D@T_A=25^\circ C$	Total Power Dissipation <sup>4</sup>	3.1	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ C$

## Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient <sup>1</sup>	---	40	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	---	24	$^\circ C/W$

**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	100	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =1mA	---	0.098	---	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =11.5A	---	8.9	11	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =9.5A	---	9.9	13	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.4	1.7	2.5	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	-5.52	---	mV/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =100V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	uA
		V <sub>DS</sub> =100V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C	---	---	5	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
R <sub>g</sub>	Gate Resistance	V <sub>DS</sub> =0V, V <sub>GS</sub> =0V, f=1MHz	---	0.55	1.0	Ω
Q <sub>g</sub>	Total Gate Charge (10V)	V <sub>DS</sub> =50V, V <sub>GS</sub> =10V, I <sub>D</sub> =11.5A	---	15	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	7	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	4	---	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =50V, V <sub>GEN</sub> =10V, R <sub>G</sub> =3Ω, I <sub>D</sub> =1A, R <sub>L</sub> =4.35Ω	---	3	---	ns
T <sub>r</sub>	Rise Time		---	8	---	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	4	---	
T <sub>f</sub>	Fall Time		---	25	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =50V, V <sub>GS</sub> =0V, f=1MHz	---	4000	---	pF
C <sub>oss</sub>	Output Capacitance		---	898	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	39	---	

**Guaranteed Avalanche Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy <sup>5</sup>	V <sub>DD</sub> =50V, L=0.1mH, I <sub>AS</sub> =10A	18	---	---	mJ

**Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current <sup>1,6</sup>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	4	A
I <sub>SM</sub>	Pulsed Source Current <sup>2,6</sup>		---	---	16	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =6A, T <sub>J</sub> =25°C	---	---	1.1	V
t <sub>rr</sub>	Reverse Recovery Time	IF=1A, dI/dt=100A/μs, T <sub>J</sub> =25°C	---	25	---	nS
Q <sub>rr</sub>	Reverse Recovery Charge		---	110	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 20Z copper, t<10sec.
- 2.The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- 3.The EAS data shows Max. rating. The test condition is V<sub>DD</sub>=25V, V<sub>GS</sub>=10V, L=0.1mH, I<sub>AS</sub>=10A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The Min. value is 100% EAS tested guarantee.
- 6.The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub>, in real applications, should be limited by total power dissipation.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

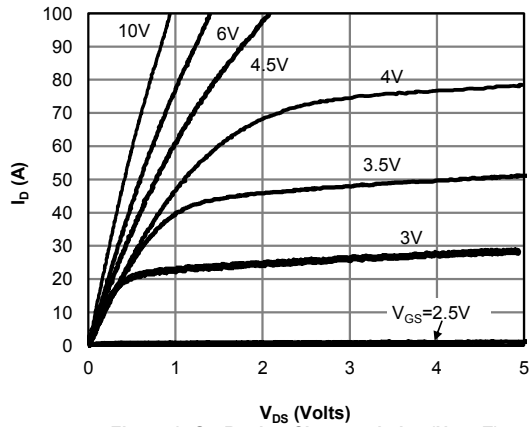


Figure 1: On-Region Characteristics (Note E)

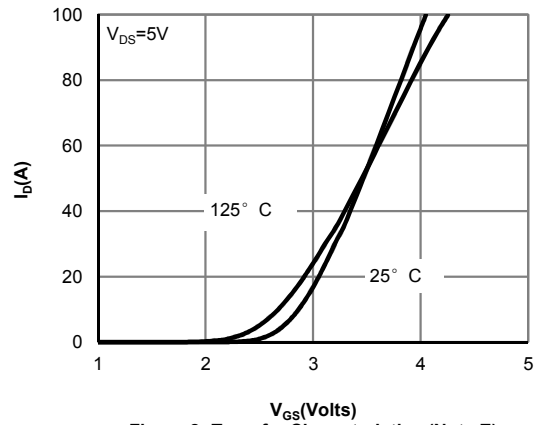


Figure 2: Transfer Characteristics (Note E)

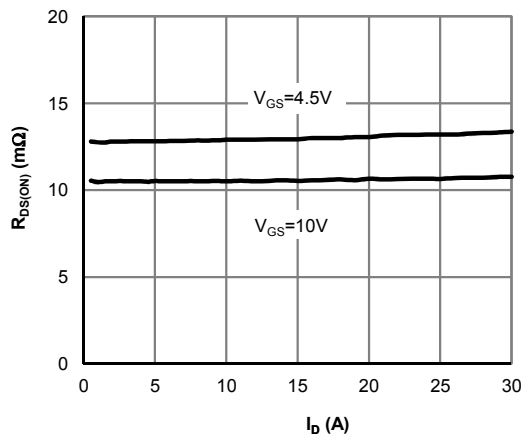


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

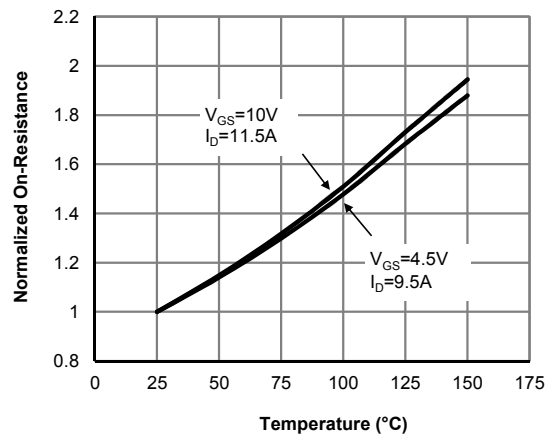


Figure 4: On-Resistance vs. Junction Temperature (Note E)

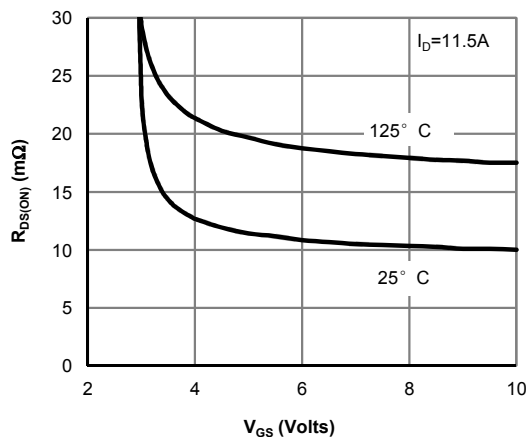


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

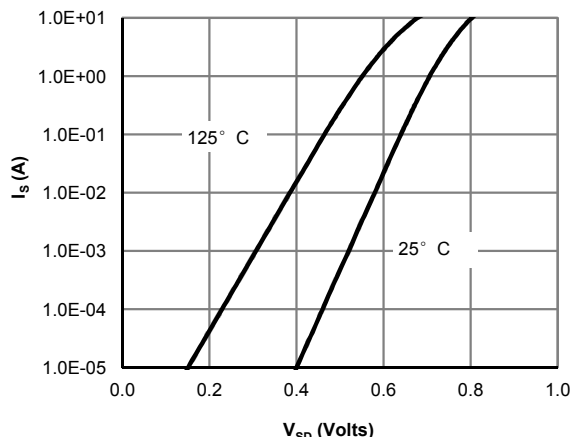
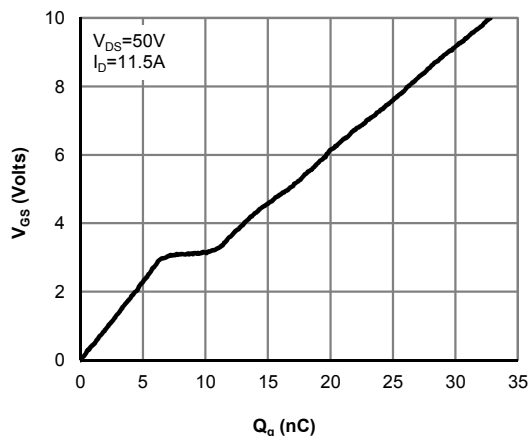
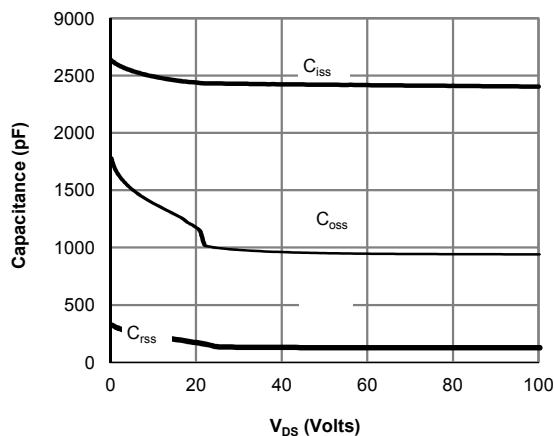
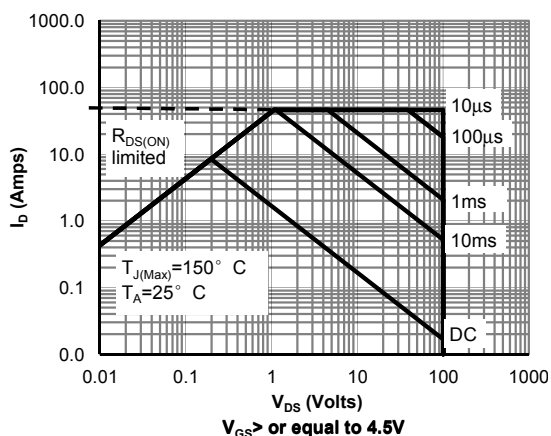
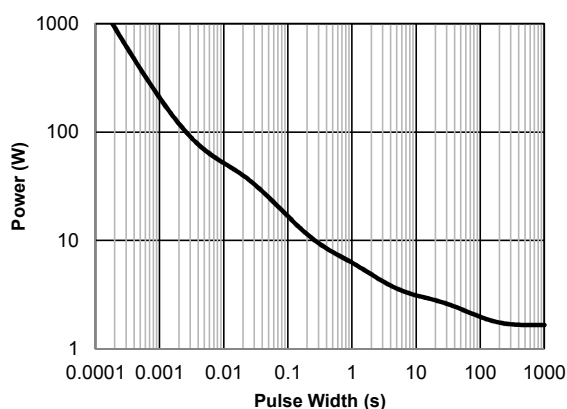
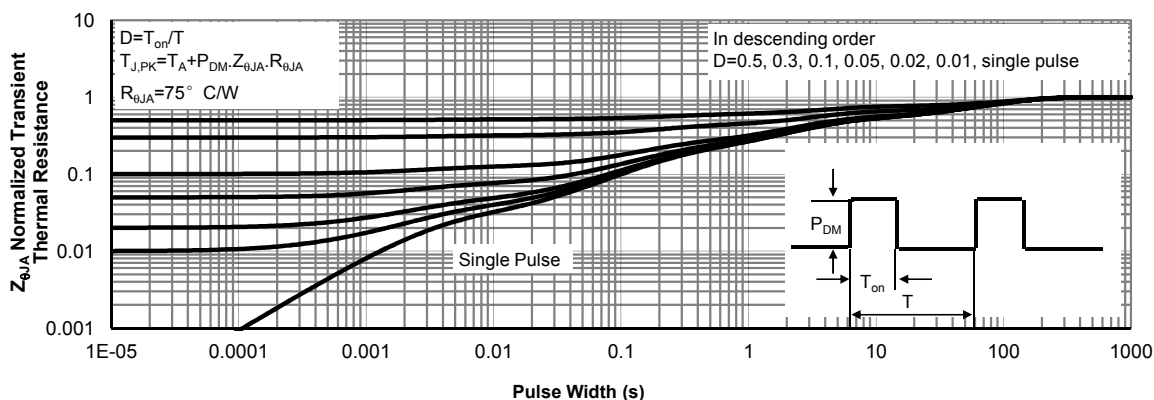
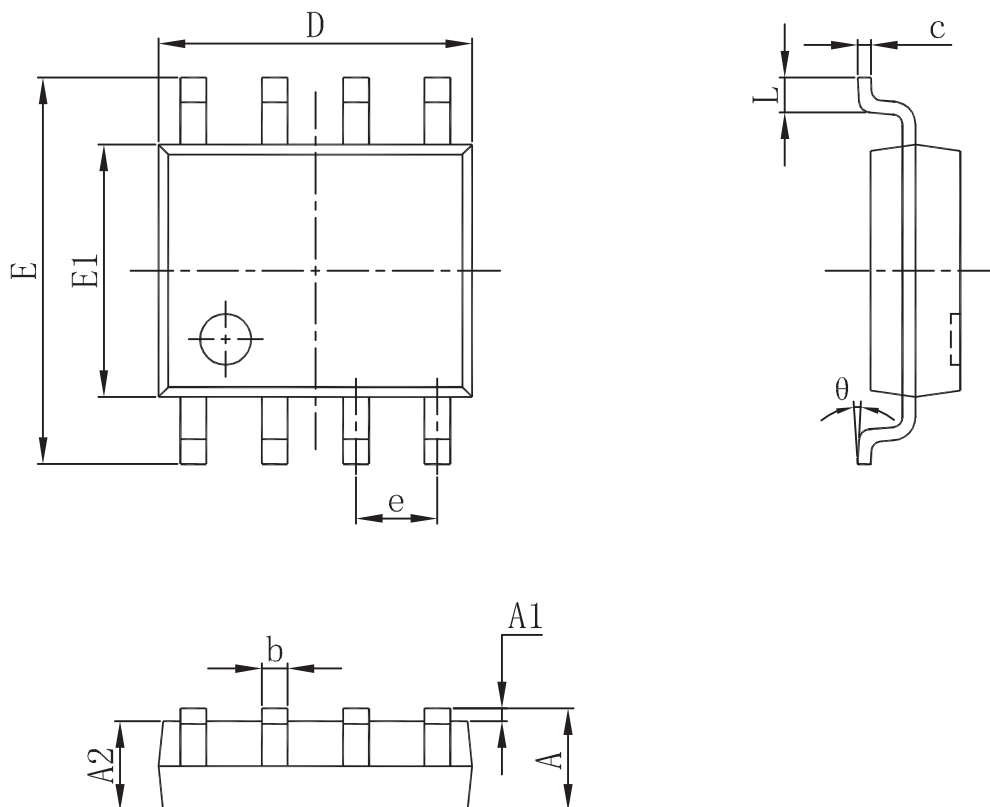


Figure 6: Body-Diode Characteristics (Note E)

**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**

**Figure 7: Gate-Charge Characteristics**

**Figure 8: Capacitance Characteristics**

**Figure 9: Maximum Forward Biased Safe Operating Area (Note F)**

**Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)**

**Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)**

## Packaging information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.800	5.000	0.189	0.197
e	1.270 (BSC)		0.050 (BSC)	
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

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